

A2: LIST OF DISSEMINATION ACTIVITIES

NO.	Type of activities ³	Main leader	Title	Date/Period	Place	Type of audience ⁴	Size of audience	Countries addressed
IEE								
1	Conference	Gregušová, D.	“Controlled barrier oxidation and 100 °C ALD for a gate insulation: a way towards high-performance normally-off GaN HEMTs?”, International Conference on Nitride Semiconductors	August 25-30, 2013	Washington, USA	Scientific Community	900	worldwide
2	Conference	Gregušová, D.	“Normally-off AlGaIn/GaN HEMTs with plasma oxidation and 100 °C ALD gate insulation”, Topical Workshop on Heterostructure Materials	September 2-5, 2013	Hakodate, Japan	Scientific Community	200	worldwide
3	Conference	Kuzmik, J.	Expert Evaluation and Control of Compound Semiconductor Materials and Technologies	June 15-20, 2014	Delphi, Greece	Scientific Community	150	worldwide
4	Conference	Ťapajna, M.	Advanced Semiconductor Devices and Microsystems	October 20-22, 2014	Smolenice Castle, Slovakia	Scientific Community	100	worldwide

³ A drop down list allows choosing the dissemination activity: publications, conferences, workshops, web, press releases, flyers, articles published in the popular press, videos, media briefings, presentations, exhibitions, thesis, interviews, films, TV clips, posters, Other.

⁴ A drop down list allows choosing the type of public: Scientific Community (higher education, Research), Industry, Civil Society, Policy makers, Medias, Other ('multiple choices' is possible).

5	Conference	Tapajna, M.	"Control of threshold voltage in GaN based MOS-HEMTs towards the normally-off operation" in International Workshop on Nitride Semiconductors	October 14-19, 2012	Sapporo, Japan	Scientific Community	900	worldwide
6	Conference	Tapajna, M.	"Influence of GaN cap on the electrical properties of MOS (GaN)/AlGaIn/GaN HEMT structures" in Workshop on Compound Semiconductor Devices and Integrated Circuits held in Europe	May 26-29, 2013	Warnemünde, Germany	Scientific Community	150	worldwide
7	Conference	Tapajna, M.	International Workshop on Nitride Semiconductors	August 24-29, 2014	Wroclaw, Poland	Scientific Community	900	worldwide
8	Conference	Tapajna, M.	"Impact of the buffer structure on trapping characteristics of normally-off p-GaN/AlGaIn/GaN HEMTs for power switching applications" In: ASDAM 2014	October 20-22, 2014 in	Smolenice, Slovakia	Scientific Community		worldwide
UniPd								
9	Conference	Meneghesso, G.	"GaN-HEMTs devices with single- and double-heterostructure for power switching applications," INVITED Reliability Physics Symposium (IRPS), 2013 IEEE International	14-18 April 2013	Monterey, CA, USA	Scientific Community		worldwide
10	Conference	Meneghesso, M.	"GaN-Based Power Hemts, Parasitic, Reliability and High Field Issues", Presented at the ECS Meeting INVITED	October 27-November 1, 2013	San Francisco, CA, USA	Scientific Community		worldwide

11	Conference	Meneghesso, G.	“Threshold voltage instabilities in D-mode GaN HEMTs for power switching applications”, 52nd IEEE International Reliability Physics Symposium, IRPS 2014	1-5 June 2014	Waikoloa, HI; United States	Scientific Community		worldwide
12	Conference	Meneghesso, G.	“Reliability and Instabilities in GaN-based HEMTs”, Invited 2014 IEEE International Conference on Electron Devices and Solid-State Circuits (EDSSC)	18 June - 20 June 2014	Chengdu, China	Scientific Community		worldwide
13	Conference	Meneghesso, G.	“Reliability and High Field related issues in GaN-HEMT devices”, Invited Tutorial 2nd IEEE Workshop on Wide Bandgap Power Devices and Applications (WIPDA2014)	Oct. 13-15, 2014	Knoxville, Tennessee, USA	Scientific Community		worldwide
14	Conference	Meneghesso, G.	“Trapping and High Field Related Issues in GaN Power HEMTs”, INVITED, Proc. of IEEE International Electron Device Meeting IEDM 2014	December 15-17, 2014	San Francisco, CA	Scientific Community		worldwide
15	Conference	Meneghini, M.	“Comparison of breakdown characteristics of Al-GaN/GaN HEMTs in voltage and current controlled mode : electrical and optical characterization”, TWHM2013, 10th Topical Workshop on Heterostructure Microelectronics	September 2-5, 2013	Hakodate, Japan	Scientific Community	200	worldwide

16	Conference	Meneghini, M.	“Reliability and Parasitic Effects of GaN HEMTs”, IIRW 2013, IEEE International Integrated Reliability Workshop	13 Oct - 17 Oct 2013	Lake Tahoe, CA, USA	Scientific Community		worldwide
17	Conference	Meneghini, M.	“GaN-based HEMTs for power applications: parasitics and reliability”, INVITED TUTORIAL at 2014 IEEE International Reliability Physics Symposium (IRPS)	June 1-5, 2014	Waikoloa, HI, USA	Scientific Community		worldwide
18	Conference	Meneghini, M.	“GaN-based HEMTs for power applications: parasitics and reliability” INVITED TUTORIAL Wide-Bandgap Materials for Solid-State Lighting and Power Electronics, 2014 MRS Fall Meeting & Exhibit	November 30 - December 5, 2014	Boston, Massachusetts, USA	Scientific Community		worldwide
19	Conference	Meneghini, M.	“GaN-based devices: technology, physics and reliability”, INVITED Emerging Technology Seminar at EOS/ESD Symposium 2014	September 8, 2014,	Westin La Paloma, Tucson AZ	Scientific Community		worldwide
20	Conference	Zanoni, E.	“Reliability of Gallium Nitride High Electron Mobility Transistors: from microwave to power electronics” Invited TUTORIAL, 24th IEEE International Symposium on Power Semiconductor Devices and ICs (ISPSD'12)	June 4-7, 2012	Bruges, Belgium	Scientific Community		worldwide

21	Conference	Zanoni, E.	“Physical effects limiting performance and reliability of GaN High Electron Mobility Transistors”, INVITED International Conference on Solid State Devices and Materials (SSDM), ,	08-11 Sep 2014	Tsukuba, Japan	Scientific Community		worldwide
22	Conference	Zanoni, E.	“Reliability issues in GaN-based HEMTs: from charge trapping to failure mechanisms”, INVITED, Presented at the International Workshop on Nitride Semiconductors IWN-2014	August 24-29 2014	Wroclaw, Poland	Scientific Community	900	worldwide
TU Vienna								
23	Conference	Alexewicz, A.	“Gate oxides for Al-GaN/GaN HEMTs on Si substrate”, In: Workshop on Compound Semiconductor Materials & Devices (WOCSEMMAD) 2013	February 17-20, 2013	New Orleans, Louisiana	Scientific Community		worldwide
24	Conference	Alexewicz, A.	“GaN MOSHEMTs with thin barrier on Si substrate”, In: Joint Annual Meeting of the Austrian and Swiss Physical Societies 2013	September 3-6, 2013	Linz, Austria	Scientific Community		worldwide
25	Conference	Capriotti, M.	“Comparison of MOS and Schottky-barrier structure in AlGaIn/GaN HEMTs” ÖPG2012	Sep 18 - 21, 2012	Graz, Austria	Scientific Community		worldwide

26	Conference	Capriotti, M.	"AlGaIn/GaN MOSHEMTs with selective removal of in-situ grown SiN passivation", In: Workshop on Compound Semiconductor Devices and Integrated Circuits held in Europe (WOCSDICE) 2013	May 26-29, 2013	Warnemünde, Germany	Scientific Community	150	worldwide
27	Conference	Capriotti, M.	"Different layer designs for normally off GaN HEMTs with ultrathin AlN barrier GaN cap and in situ SiN passivation", WOCSDICE 2014,	June 15-20, 2014	Delphi, Greece	Scientific Community		worldwide
28	Conference	Fleury, C.	"Localization of vertical breakdown spots in normally-off and normally-on AlGaIn/GaN HEMTs on SiC and Si substrates. WOCSDICE 2013	May 26-29, 2013	Warnemunde, Germany	Scientific Community	150	worldwide
29	Conference	Fleury, C.	Transient thermal mapping of p-GaN gate normally-off AlGaIn/GaN transistors. WOCSDICE 2013	May 26-29, 2013	Warnemunde, Germany	Scientific Community	150	worldwide
30	Conference	Fleury, C.	"Temperature extraction in normally-off AlGaIn HEMTs using transient interferometric mapping", WOCSDICE 2014 (38 th Workshop on Compound Semiconductors Devices and integrated circuits"	June 15-20, 2014	Delphi, Greece	Scientific Community		worldwide

FBH								
31	Press release	FBH	"More efficiency for power electronics"	November, 2011		Scientific Community		worldwide
32	Website	FBH	www.hiposwitch.eu	November, 2011		Scientific Community		worldwide
33	Conference	Badawi, N.	"Switching Characteristics of 200 V Normally-off GaN HEMTs", Int. Exhibition and Conf. for Power Electronics, Intelligent Motion, Renewable Energy and Energy Management (PCIM Europe)	May 14-16, 2013	Nuremberg, Germany	Scientific Community		worldwide
34	Conference	Badawi, N.	"Switching Performance of 400 V Normally-On and Normally-Off GaN HEMTs", 37th Workshop on Compound Semiconductor Devices and Integrated Circuits (WOCSDICE)	May 26-29, 2013	Warnemünde, Germany	Scientific Community	150	worldwide
35	Conference	Bahat-Treidel, E.	"AlGaIn/GaN/AlGaIn/GaN:C on N-SiC Power HEMT with Low Switching Dynamic RON and High Breakdown Voltage", 37th Workshop on Compound Semiconductor Devices and Integrated Circuits (WOCSDICE)	May 26-29, 2013	Warnemünde, Germany	Scientific Community	150	worldwide

36	Conference	Bahat-Treidel, E.	„Systematic study of GaN based power transistors' dynamic on state resistance at elevated temperatures“, Proc. 41th Int. Symp. on Compound Semiconductors (ISCS)	11-15 May 2014	Montpellier, France	Scientific Community		worldwide
37	Conference	Hilt, O.	“Normally-off GaN Transistors and Diodes for Power Applications“, 3 rd Global COE Int. Symp. Electronic Devices Innovation (EDIS 2011)	16-17 Dec., 2011	Osaka, Japan	Scientific Community		worldwide
38	Conference	Hilt, O.	“Impact of Buffer Composition on the Dynamic On-State Resistance of High-Voltage AlGaIn/GaN HFETs“, 24th Int. Symp. on Power Semiconductor Devices and ICs (ISPSD)	03.06 - 07.06.2012	Bruges, Belgium	Scientific Community		worldwide
39	Conference	Hilt, O.	“Normally-off GaN Transistors for Power Applications“, Microtechnology and Thermal Problems in Electronics (MicroTherm) 2013	26. 06.- 28.06.2013	Lodz, Poland	Scientific Community		worldwide
40	Conference	Hilt, O.	"Normally-off GaN Transistors for Power Switching Applications", 224th ECS Meeting	27.10.- 01.11.2013	San Francisco, USA	Scientific Community		worldwide
41	Conference	Hilt, O.	“Selbstsperrende GaN Transistoren für Anwendungen in der Leistungselektronik“, DLR Bauteilekonferenz	09.04.- 10.04.2014	Freiburg, Germany	Scientific Community		worldwide

42	Conference	Hilt, O.	„The HiPoSwitch Project – Device Technology“, 44th European Solid-State Device Research Conference (ESSDERC)	22.09.- 26.09. 2014	Venice, Italy	Scientific Community		worldwide
43	Conference	Kotara, P.	“Improvement of vertical breakdown using pre-epitaxial implantation on n-SiC substrates”, 36th Workshop on Compound Semiconductor Devices and Integrated Circuits (WOCSDICE), 2012	28-30 May, 2012	Island of Porquerolles (France)	Scientific Community		worldwide
44	Conference	Würfl, J.	"GaN Power Devices (HEMT): Basics, Advantages and Perspectives", ECPE Workshop: SiC & GaN User Forum 'Potential of Wide Bandgap Semiconductors in Power Electronic Applications	May 2-3, 2013	Munich, Germany	Scientific Community		worldwide
45	Conference	Würfl, J.	"Power Electronic Devices based on GaN: Advantages and Perspectives", Int. Conf. and Exhibition on Automotive Power Electronics	Apr. 3-4, 2013	Paris, France	Scientific Community		worldwide
46	Conference	Würfl, J.	"Breakdown and dynamic effects in GaN power switching devices", INVITED presentation at CSW	19-23 May, 2013	Kobe, Japan	Scientific Community		worldwide

47	Conference	Würfl, J.	“Overview on Project ‘GaN-Based Normally-Off High Power Switching Transistors for Efficient Power Converters’ (HIPOSWITCH)”, 37th Workshop on Compound Semiconductor Devices and Integrated Circuits (WOCSDICE)	May 26-29, 2013	Warnemünde, Germany	Scientific Community	150	worldwide
48	Conference	Würfl, J.	“European GaN Device Technologies for Microwave and Power Switching Applications”, INVITED presentation at the Asia Pacific Microwave Conference (APMC),		Sendai, Japan	Scientific Community		worldwide
49	Conference	Würfl, J.	“GaN microwave and high power switching devices: Status and perspectives at FBH”, 7th Wide Band Gap Semiconductor and Components Workshop			Scientific Community		worldwide
50	Conference	Würfl, J.	“Drift and reliability mechanisms in GaN based power devices for high voltage switching applications: The current understanding”, INVITED Tutorial at the 25th European Symposium on Reliability of Electron Devices, Failure Physics and Analysis 2014 (ESREF)	2014		Scientific Community		worldwide

51	Conference	Zhytnytska, R.	"Comparison of vertical breakdown properties of C-doped GaN and AlGaIn buffer structures on conductive SiC substrates" on 36th Workshop on Compound Semiconductor Devices and Integrated Circuits (WOCSDICE) 2012	28-30 May, 2012	Island of Porquerolles (France)	Scientific Community		worldwide
52	Conference	Zhytnytska, R.	"Influence of Device Periphery Design on Breakdown and On-State Resistance of AlGaIn/GaN HEMTs", 37th Workshop on Compound Semiconductor Devices and Integrated Circuits (WOCSDICE)	May 26-29, 2013	Warnemünde, Germany	Scientific Community	150	worldwide
AIXTRON								
53	Conference	Giesen, C.	16th International Conference on Metalorganic Vapor Phase Epitaxy	20.-25. May 2012	Busan, South Korea	Scientific Community	350	worldwide
54	Conference	Giesen, C.	LED/Si tuning in a 200 mm diameter planetary reactor", 37th Workshop on Compound Semiconductor Devices and Integrated Circuits (WOCSDICE)	May 26-29, 2013	Warnemünde, Germany	Scientific Community	150	worldwide

EpiGaN								
55	Conference	Derluyn, J.	“GaN Epitaxy on 200 mm Si substrates for power switching applications”, 37th Workshop on Compound Semiconductor Devices and Integrated Circuits (WOCSDICE)	May 26-29, 2013	Warnemünde, Germany	Scientific Community	150	worldwide